(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
26 February 2004 (26.02.2004)

PCT

(10) International Publication Number
WO 2004/017383 A3

(51) International Patent Classification[7]: H01L 21/31

(21) International Application Number:
PCT/US2003/026083

(22) International Filing Date: 18 August 2003 (18.08.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
60/404,363 18 August 2002 (18.08.2002) US

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(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

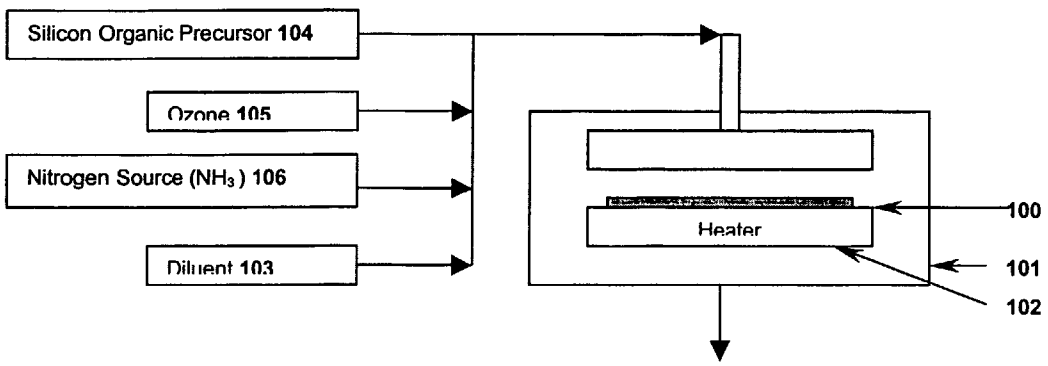
(84) Designated States *(regional)*: ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*
— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

(88) Date of publication of the international search report:
22 July 2004

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: LOW TERMPERATURE DEPOSITION OF SILICON OXIDES AND OXYNITRIDES



(57) Abstract: The present invention relates to low temperature (i.e., less than about 450 °C) chemical vapor deposition (CVD) and low temperature atomic layer deposition (ALD) processes for forming silicon oxide and/or silicon oxynitride derived from silicon organic precursors and ozone. The processes of the invention provide good step coverage. The invention can be utilized to deposit both high-k and low-k dielectrics.

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